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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f101ret6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4, TIM5	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

 Table 4. Timer feature comparison

General-purpose timers (TIMx)

There are up to 4 synchronizable general-purpose timers (TIM2, TIM3, TIM4 and TIM5) embedded in the STM32F101xC, STM32F101xD and STM32F101xE access line devices. These timers are based on a 16-bit auto-reload up/down counter, a 16-bit prescaler and feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input captures / output compares / PWMs on the largest packages.

The general-purpose timers can work together with the advanced-control timer via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs. They all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as a generic 16-bit time base.

Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.



SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.18 I²C bus

Up to two I²C bus interfaces can operate in multi-master and slave modes. They support standard and fast modes.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded. They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.19 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F101xC, STM32F101xD and STM32F101xE access line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. The five interfaces are able to communicate at speeds of up to 2.25 Mbit/s.

USART1, USART2 and USART3 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller except for UART5.

2.3.20 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

All SPIs can be served by the DMA controller.

2.3.21 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.



	Pins						Alternate functions ⁽⁴⁾	
LQFP144	LQFP64	LQFP100	Pin name	Type ⁽¹⁾	I / O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Default	Remap
12	-	-	PF2	I/O	FT	PF2	FSMC_A2	-
13	-	-	PF3	I/O	FT	PF3	FSMC_A3	-
14	-	-	PF4	I/O	FT	PF4	FSMC_A4	-
15	-	-	PF5	I/O	FT	PF5	FSMC_A5	-
16	-	10	V _{SS_5}	S	-	V _{SS_5}	-	-
17	-	11	V _{DD_5}	S	-	V _{DD_5}	-	-
18	-	-	PF6	I/O	-	PF6	FSMC_NIORD	-
19	-	-	PF7	I/O	-	PF7	FSMC_NREG	-
20	-	-	PF8	I/O	-	PF8	FSMC_NIOWR	-
21	-	-	PF9	I/O	-	PF9	FSMC_CD	-
22	-	-	PF10	I/O	-	PF10	FSMC_INTR	-
23	5	12	OSC_IN	Ι	-	OSC_IN	-	PD0 ⁽⁷⁾
24	6	13	OSC_OUT	0	-	OSC_OUT	-	PD1 ⁽⁷⁾
25	7	14	NRST	I/O	-	NRST	-	-
26	8	15	PC0	I/O	-	PC0	ADC_IN10	-
27	9	16	PC1	I/O	-	PC1	ADC_IN11	-
28	10	17	PC2	I/O	-	PC2	ADC_IN12	-
29	11	18	PC3	I/O	-	PC3	ADC_IN13	-
30	12	19	V _{SSA}	S	-	V _{SSA}	-	-
31	-	20	V _{REF-}	S	-	V _{REF-}	-	-
32	-	21	V _{REF+}	S	-	V _{REF+}	-	-
33	13	22	V _{DDA}	S	-	V _{DDA}	-	-
34	14	23	PA0-WKUP	I/O	-	PA0	WKUP/ USART2_CTS ⁽⁸⁾ / ADC_IN0/TIM5_CH1/ TIM2_CH1_ETR ⁽⁸⁾	-
35	15	24	PA1	I/O	-	PA1	USART2_RTS ⁽⁸⁾ / ADC_IN1/TIM5_CH2 TIM2_CH2 ⁽⁸⁾	-
36	16	25	PA2	I/O	-	PA2	USART2_TX ⁽⁸⁾ / TIM5_CH3/ADC_IN2/ TIM2_CH3 ⁽⁸⁾	-

	Table 5.	STM32F101xC/STM32F101xD/STM32F101xE	pin definitions	(continued)
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	Pins						Alternate functions ⁽⁴⁾	
LQFP144	LQFP64	LQFP100	Pin name	Type ⁽¹⁾	I / O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Default	Remap
62	-	-	V _{DD_7}	S	-	V _{DD_7}	-	-
63	-	41	PE10	I/O	FT	PE10	FSMC_D7	-
64	-	42	PE11	I/O	FT	PE11	FSMC_D8	-
65	-	43	PE12	I/O	FT	PE12	FSMC_D9	-
66	-	44	PE13	I/O	FT	PE13	FSMC_D10	-
67	-	45	PE14	I/O	FT	PE14	FSMC_D11	-
68	-	46	PE15	I/O	FT	PE15	FSMC_D12	-
69	29	47	PB10	I/O	FT	PB10	I2C2_SCL/ USART3_TX ⁽⁸⁾	TIM2_CH3
70	30	48	PB11	I/O	FT	PB11	I2C2_SDA/ USART3_RX ⁽⁸⁾	TIM2_CH4
71	31	49	V _{SS_1}	S	-	V _{SS_1}	-	-
72	32	50	V _{DD_1}	S	-	V _{DD_1}	-	-
73	33	51	PB12	I/O	FT	PB12	SPI2_NSS ^{(8)/} I2C2_SMBA USART3_CK ⁽⁸⁾	-
74	34	52	PB13	I/O	FT	PB13	SPI2_SCK ⁽⁸⁾ / USART3_CTS ⁽⁸⁾	-
75	35	53	PB14	I/O	FT	PB14	SPI2_MISO ⁽⁸⁾ / USART3_RTS ⁽⁸⁾	-
76	36	54	PB15	I/O	FT	PB15	SPI2_MOSI ⁽⁸⁾	-
77	-	55	PD8	I/O	FT	PD8	FSMC_D13	USART3_TX
78	-	56	PD9	I/O	FT	PD9	FSMC_D14	USART3_RX
79	-	57	PD10	I/O	FT	PD10	FSMC_D15	USART3_CK
80	-	58	PD11	I/O	FT	PD11	FSMC_A16	USART3_CTS
81	-	59	PD12	I/O	FT	PD12	FSMC_A17	TIM4_CH1 / USART3_RTS
82	-	60	PD13	I/O	FT	PD13	FSMC_A18	TIM4_CH2
83	-	-	V _{SS_8}	S	-	V _{SS_8}	-	-
84	-	-	V _{DD_8}	S	-	V _{DD_8}	-	
85	-	61	PD14	I/O	FT	PD14	FSMC_D0	TIM4_CH3
86	-	62	PD15	I/O	FT	PD15	FSMC_D1	TIM4_CH4
87	-	-	PG2	I/O	FT	PG2	FSMC_A12	-

Table 5. STM32F101xC/STM32F101xD/STM32F101xE pin definitions (continued)



5.1.7 Current consumption measurement



Figure 10. Current consumption measurement scheme

5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 7: Voltage characteristics*, *Table 8: Current characteristics*, and *Table 9: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Symbol	Ratings	Min	Max	Unit	
$V_{DD} - V_{SS}$	External main supply voltage (including V_{DDA} and $V_{DD})^{\left(1\right)}$	-0.3	4.0		
V (2)	Input voltage on five volt tolerant pin	$V_{SS} - 0.3$	V _{DD} + 4.0	V	
VIN' /	Input voltage on any other pin	$V_{SS} - 0.3$	4.0		
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50		
V _{SSX} – V _{SS}	Variations between all the different ground pins	-	50	mV	
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	see Section 5.3.12: Absolute maximum ratings (electrical sensitivity)			

Table 7. Voltage characteristics

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.

2. V_{IN} maximum must always be respected. Refer to *Table 8: Current characteristics* for the maximum allowed injected current values.





Figure 13. Typical current consumption on $\rm V_{BAT}$ with RTC on vs. temperature at different $\rm V_{BAT}$ values

Figure 14. Typical current consumption in Stop mode with regulator in run mode versus temperature at different V_{DD} values





		Conditions		Typ ⁽¹⁾	Typ ⁽¹⁾	
Symbol	Parameter		f _{HCLK}	All peripherals enabled ⁽²⁾	All peripherals disabled	Unit
			36 MHz	15.1	3.6	
			24 MHz	10.4	2.6	
			16 MHz	7.2	2	
			8 MHz	3.9	1.3	
		External clock ⁽³⁾	4 MHz	2.6	1.2	
	Supply current in Sleep mode		2 MHz	1.85	1.15	
			1 MHz	1.5	1.1	
			500 kHz	1.3	1.05	
			125 kHz	1.2	1.05	m۸
DD		e Running on High Speed Internal	36 MHz	14.5	3	ШA
			24 MHz	9.8	2	
			16 MHz	6.6	1.4	
			8 MHz	3.3	0.7	
		RC (HSI), AHB prescaler used to	4 MHz	2	0.6	
		reduce the	2 MHz	1.25	0.55	
		frequency	1 MHz	0.9	0.5	
			500 kHz	0.7	0.45	
			125 kHz	0.6	0.45	

Table 19. Typical current consumption in Sleep mode, code running from Flash or RAM

1. Typical values are measures at $T_A = 25 \text{ °C}$, $V_{DD} = 3.3 \text{ V}$.

2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).

3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 20*. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- ambient operating temperature and V_{DD} supply voltage conditions summarized in Table 7.



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 23*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	16	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
С	Recommended load capacitance versus equivalent serial resistance of the crystal $(R_S)^{(3)}$	R _S = 30 Ω	-	30	-	pF
i ₂	HSE driving current	V_{DD} = 3.3 V V_{IN} = V_{SS} with 30 pF load	-	-	1	mA
9 _m	Oscillator transconductance	Startup	25	-	-	mA/V
t _{SU(HSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	2	-	ms

Fable 23. HSE 4-16 MHz oscillator characteristics ⁽¹)(2	2)
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1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by characterization results, not tested in production

3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.

4. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 19*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website *www.st.com*.





Figure 21. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

1. Mode 2/B, C and D only. In Mode 1, FSMC_NADV is not used.

FSMC_BusTurnAroundDuration = 0.

Table 31. Asynchronous r	non-multiplexed SRAM/PSRAM/NOR	R read timings ^{(1) (2)}
······		

Symbol	Parameter	Min	Мах	Unit
t _{w(NE)}	FSMC_NE low time	5t _{HCLK} – 1.5	5t _{HCLK} + 2	ns
t _{v(NOE_NE)}	FSMC_NEx low to FSMC_NOE low	0.5	1.5	ns
t _{w(NOE)}	FSMC_NOE low time	5t _{HCLK} – 1.5	5t _{HCLK} + 1.5	ns
t _{h(NE_NOE)}	FSMC_NOE high to FSMC_NE high hold time	-1.5	-	ns
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	7	ns
t _{h(A_NOE)}	Address hold time after FSMC_NOE high	0.1	-	ns
t _{v(BL_NE)}	FSMC_NEx low to FSMC_BL valid	-	0	ns
t _{h(BL_NOE)}	FSMC_BL hold time after FSMC_NOE high	0	-	ns
t _{su(Data_NE)}	Data to FSMC_NEx high setup time	2t _{HCLK} + 25	-	ns
t _{su(Data_NOE)}	Data to FSMC_NOEx high setup time	2t _{HCLK} + 25	-	ns
t _{h(Data_NOE)}	Data hold time after FSMC_NOE high	0	-	ns

Note:





Figure 24. Asynchronous multiplexed NOR/PSRAM write waveforms

Table 34. As	ynchronous mult	iplexed NOR/PSRAM	write timings ⁽¹⁾⁽²⁾
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Symbol	Parameter	Min	Мах	Unit
t _{w(NE)}	FSMC_NE low time	5t _{HCLK} – 1	5t _{HCLK} + 2	ns
t _{v(NWE_NE)}	FSMC_NEx low to FSMC_NWE low	1t _{HCLK}	1t _{HCLK} + 1	ns
t _{w(NWE)}	FSMC_NWE low time	3t _{HCLK} – 1	2	ns
t _{h(NE_NWE)}	FSMC_NWE high to FSMC_NE high hold time	t _{HCLK} – 1	-	ns
t _{v(A_NE)}	FSMC_NEx low to FSMC_A valid	-	7	ns
t _{v(NADV_NE)}	FSMC_NEx low to FSMC_NADV low	3	5	ns
t _{w(NADV)}	FSMC_NADV low time	t _{HCLK} – 1	t _{HCLK} + 1	ns
t _{h(AD_NADV)}	FSMC_AD (address) valid hold time after FSMC_NADV high	t _{HCLK} – 3	-	ns
t _{h(A_NWE)}	Address hold time after FSMC_NWE high	1t _{HCLK}	-	ns
t _{v(BL_NE)}	FSMC_NEx low to FSMC_BL valid	-	1.6	ns
$t_{h(BL_NWE)}$	FSMC_BL hold time after FSMC_NWE high	t _{HCLK} – 1.5	-	ns
t _{v(Data_NADV)}	FSMC_NADV high to Data valid	-	t _{HCLK} + 1.5	ns
t _{h(Data_NWE)}	Data hold time after FSMC_NWE high	t _{HCLK} – 5	-	ns

1. C_L = 15 pF.

2. Guaranteed by characterization results, not tested in production..







Figure 29. PC Card/CompactFlash controller waveforms for common memory read access

1. FSMC_NCE4_2 remains high (inactive during 8-bit access.





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Figure 38. NAND controller waveforms for common memory write access

Symbol	Parameter	Min	Max	Unit
t _{d(D-NWE)} ⁽²⁾	FSMC_D[15:0] valid before FSMC_NWE high	5t _{HCLK} + 12	-	ns
t _{w(NOE)} ⁽²⁾	FSMC_NOE low width	4t _{HCLK} – 1.5	4t _{HCLK} + 1.5	ns
t _{su(D-NOE)} (2)	FSMC_D[15:0] valid data before FSMC_NOE high	25	-	ns
t _{h(NOE-D)} ⁽²⁾	FSMC_D[15:0] valid data after FSMC_NOE high	7	-	ns
t _{w(NWE)} ⁽²⁾	FSMC_NWE low width	4t _{HCLK} – 1	4t _{HCLK} + 2.5	ns
t _{v(NWE-D)} ⁽²⁾	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
t _{h(NWE-D)} ⁽²⁾	FSMC_NWE high to FSMC_D[15:0] invalid	2t _{HCLK} + 4ns	-	ns
$t_{d(ALE-NWE)}^{(3)}$	FSMC_ALE valid before FSMC_NWE low	-	3t _{HCLK} + 1.5	ns
$t_{h(NWE-ALE)}^{(3)}$	FSMC_NWE high to FSMC_ALE invalid	3t _{HCLK} + 4.5	-	ns
t _{d(ALE-NOE)} ⁽³⁾	FSMC_ALE valid before FSMC_NOE low	-	3t _{HCLK} + 2	ns
t _{h(NOE-ALE)} ⁽³⁾	FSMC_NWE high to FSMC_ALE invalid	3t _{HCLK} + 4.5	-	ns

1. C_L = 15 pF.

2. Guaranteed by characterization results, not tested in production.

3. Guaranteed by design, not tested in production.

5.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.



5.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 46* are derived from tests performed under the conditions summarized in *Table 10*. All I/Os are CMOS and TTL compliant.

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V	Standard IO input low level voltage		-0.3		0.28*(V _{DD} -2 V)+0.8 V	V
VIL	IO FT ⁽¹⁾ input low level voltage	-	-0.3		0.32*(V _{DD} -2V)+0.75 V	V
	Standard IO input high level voltage		0.41*(V _{DD} -2 V)+1.3 V		V _{DD} +0.3	V
V _{IH}	IO FT ⁽¹⁾ input high level	V _{DD} > 2 V	0.42*(\/2 \/)+1 \/		5.5	V
	voltage	$V_{DD} \le 2 V$	0.42 (000-2 0) 1 0		5.2	v
V _{hys}	Standard IO Schmitt trigger voltage hysteresis ⁽²⁾	-	200		-	mV
	IO FT Schmitt trigger voltage hysteresis ⁽²⁾		5% V _{DD} ⁽³⁾		-	mV
L.	Input leakage current ⁽⁴⁾	$\begin{array}{c c} & V_{SS} \leq V_{IN} \leq V_{DD} \\ & Standard I/Os \end{array} - \pm 1 \end{array}$		±1		
'lkg		V _{IN} = 5 V I/O FT	-		3	μΛ
R _{PU}	Weak pull-up equivalent resistor ⁽⁵⁾	$V_{IN} = V_{SS}$	30	40	50	kΩ
R _{PD}	Weak pull-down equivalent resistor ⁽⁵⁾	$V_{IN} = V_{DD}$	30	40	50	kΩ
C _{IO}	I/O pin capacitance	-	-	5	-	pF

1. FT = Five-volt tolerant. In order to sustain a voltage higher than V_{DD}+0.3 the internal pull-up/pull-down resistors must be disabled.

2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results, not tested in production.

3. With a minimum of 100 mV.

4. Leakage could be higher than maximum value if negative current is injected on adjacent pins.

5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 39* and *Figure 40* for standard I/Os, and in *Figure 41* and *Figure 42* for 5 V tolerant I/Os.



Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 43* and *Table 48*, respectively.

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 10*.

MODEx [1:0] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Мах	Unit
	f _{max(IO)out}	Maximum frequency ⁽²⁾	C_L = 50 pF, V_{DD} = 2 V to 3.6 V	2	MHz
10	t _{f(IO)out}	Output high to low level fall time	C = 50 pE V = 2 V to 3 eV	125 ⁽³⁾	20
	t _{r(IO)out}	Output low to high level rise time	C _L = 30 μr, v _{DD} = 2 v to 3.0 v	125 ⁽³⁾	115
	f _{max(IO)out}	Maximum frequency ⁽²⁾	C_{L} = 50 pF, V_{DD} = 2 V to 3.6 V	10	MHz
01	t _{f(IO)out}	Output high to low level fall time		25 ⁽³⁾	
	t _{r(IO)out}	Output low to high level rise time	$C_{L} = 50 \text{ pr}, V_{DD} = 2 \text{ V to 3.6 V}$	25 ⁽³⁾	ns
	F _{max(IO)out}	Maximum Frequency ⁽²⁾	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	50	MHz
			C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	30	MHz
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	20	MHz
			C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	5 ⁽³⁾	
11	t _{f(IO)out}	Output high to low level fall time	C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	8 ⁽³⁾	
			C_L = 50 pF, V_{DD} = 2 V to 2.7 V	12 ⁽³⁾	
		t _{r(IO)out} Output low to high level rise time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	5 ⁽³⁾	ns
	t _{r(IO)out}		C_{L} = 50 pF, V_{DD} = 2.7 V to 3.6 V	8 ⁽³⁾	
			$C_{L} = 50 \text{ pF}, V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	12 ⁽³⁾	
-	t _{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	ns

Table 48. I/O AC characteristics⁽¹⁾

1. The I/O speed is configured using the MODEx[1:0] bits. Refer to the STM32F10xxx reference manual for a description of GPIO Port configuration register.

2. The maximum frequency is defined in *Figure 43*.

3. Guaranteed by design, not tested in production.



5.3.16 TIM timer characteristics

The parameters given in Table 50 are guaranteed by design.

Refer to Section 5.3.13: I/O current injection characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Parameter	Conditions	Min	Max	Unit
t maa	Timor resolution time	-	1	-	t _{TIMxCLK}
res(TIM)	Timer resolution time	f _{TIMxCLK} = 36 MHz	27.8	-	ns
f _{EXT}	Timer external clock	-	0	f _{TIMxCLK} /2	MHz
	frequency on CH1 to CH4	f _{TIMxCLK} = 36 MHz	0	18	MHz
Res_TIM	Timer resolution	-	-	16	bit
t	16-bit counter clock period	-	1	65536	t _{TIMxCLK}
^I COUNTER	selected	f _{TIMxCLK} = 36 MHz	0.0278	1820	μs
t _{MAX_COUNT}	Maximum possible count	-	-	65536 × 65536	t _{TIMxCLK}
		f _{TIMxCLK} = 36 MHz	-	119.2	s

Table 50. TIMx⁽¹⁾ characteristics

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3 and TIM4 timers.

5.3.17 Communications interfaces

I²C interface characteristics

The STM32F101xC, STM32F101xD and STM32F101xE access line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in *Table 51*. Refer also to *Section 5.3.13: I/O current injection characteristics* for more details on the input/output alternate function characteristics (SDA and SCL).



Symbol	Parameter	Standard mode I ² C ⁽¹⁾⁽²⁾		Fast mode	Unit	
		Min	Мах	Min	Max	
t _{w(SCLL)}	SCL clock low time	4.7	-	1.3	-	
t _{w(SCLH)}	SCL clock high time	4.0	-	0.6	-	μο
t _{su(SDA)}	SDA setup time	250	-	100	-	
t _{h(SDA)}	SDA data hold time	-	3450 ⁽³⁾	-	900 ⁽³⁾	
t _{r(SDA)} t _{r(SCL)}	SDA and SCL rise time	-	1000	-	300	ns
t _{f(SDA)} t _{f(SCL)}	SDA and SCL fall time	-	300	-	300	
t _{h(STA)}	Start condition hold time	4.0	-	0.6	-	
t _{su(STA)}	Repeated Start condition setup time	4.7	-	0.6	-	μs
t _{su(STO)}	Stop condition setup time	4.0	-	0.6	-	μs
t _{w(STO:STA)}	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
Cb	Capacitive load for each bus line	-	400	-	400	pF
t _{SP}	Pulse width of the spikes that are suppressed by the analog filter for standard and fast mode	0	50 ⁽⁴⁾	0	50 ⁽⁴⁾	μs

Table 51. I²C characteristics

1. Guaranteed by design, not tested in production.

f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve the fast mode I²C frequencies and it must be a multiple of 10 MHz in order to reach the I2C fast mode maximum clock speed of 400 kHz.

3. The maximum data hold time has only to be met if the interface does not stretch the low period of SCL signal.

4. The minimum width of the spikes filtered by the analog filter is above $t_{SP}(max)$.



Device marking for LQFP64

The following figure gives an example of topside marking and pin 1 position identifier location.





 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.



6.4 Thermal characteristics

The maximum chip junction temperature (T_Jmax) must never exceed the values given in *Table 10: General operating conditions on page 40*.

The maximum chip-junction temperature, $T_{\rm J}$ max, in degrees Celsius, may be calculated using the following equation:

$$T_J max = T_A max + (P_D max \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and P_{I/O} max (P_D max = P_{INT} max + P_{I/O}max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

 $P_{I/O}$ max represents the maximum power dissipation on output pins where:

 $\mathsf{P}_{\mathsf{I}/\mathsf{O}} \max = \Sigma \left(\mathsf{V}_{\mathsf{OL}} \times \mathsf{I}_{\mathsf{OL}}\right) + \Sigma((\mathsf{V}_{\mathsf{DD}} - \mathsf{V}_{\mathsf{OH}}) \times \mathsf{I}_{\mathsf{OH}}),$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Symbol	Parameter	Value	Unit
	Thermal resistance junction-ambient LQFP144 - 20 x 20 mm / 0.5 mm pitch	30	
Θ_{JA}	Thermal resistance junction-ambient LQFP100 - 14 x 14 mm / 0.5 mm pitch	46	°C/W
	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	45	

Table 64. Package thermal characteristics

6.4.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air), available from www.jedec.org.



7 Part numbering

Example:	STM32 F	101 R	С	Т	6	xxx
Device family						
STM32 = ARM [®] -based 32-bit microcontroller						
Product type						
F = general-purpose						
Device subfamily						
101 = access line						
Pin count						
R = 64 pins						
V = 100 pins						
Z = 144 pins						
Flash memory size						
C = 256 Kbytes of Flash memory						
D = 384 Kbytes of Flash memory						
E = 512 Kbytes of Flash memory						
Package						
T = LQFP						
Temperature range						
6 = Industrial temperature range, -40 to 85 °C.						
Options						

Table 65. Ordering information scheme

xxx = programmed parts

TR = tape and real

For a list of available options (speed, package, etc..) or for further information on any aspect of this device, please contact your nearest ST sales office.

